

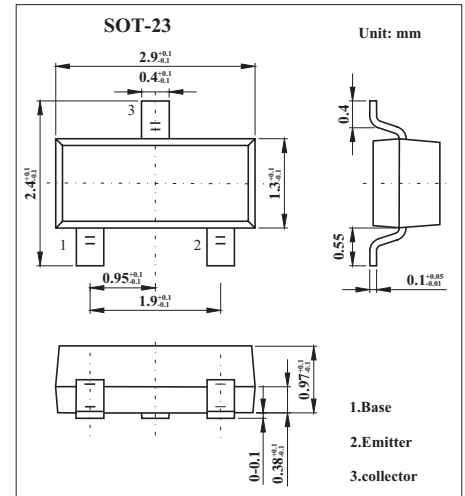
## SOT-23 Plastic-Encapsulate Transistors

### Features

- Low  $V_{CE(sat)}$ ,  $V_{CE(sat)} \leq -0.5V$  ( $I_C / I_B = -0.5A / -50mA$ ) .
- $I_C = -0.8A$ .
- PNP silicon transistor

### MECHANICAL DATA

- Case style: SOT-23 molded plastic
- Mounting position: any



## MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Unit
Collector-base Voltage	$V_{CBO}$	-40	V
Collector-emitter Voltage	$V_{CEO}$	-32	V
Emitter-base Voltage	$V_{EBO}$	-5	V
Collector current	$I_C$	-0.8	A
Collector power dissipation	$P_C$	0.2	W
Jumction temperature	$T_j$	150	°C
Storage temperature	$T_{stg}$	-55 to +150	°C

### PACKAGE INFORMATION

Device	Package	Shipping
2SB1197	SOT-23	3000/Tape&Reel

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltae	$V_{CBO}$	$I_C = -50 \mu A$	-40			V
Collector-emitter breakdown voltage	$V_{CEO}$	$I_C = -1mA$	-32			V
Emitter-base breakdown voltage	$V_{EBO}$	$I_E = -50 \mu A$	-5			V
Collector cutoff current	$I_{CBO}$	$V_{CB} = -20V$			-0.5	$\mu A$
Emitter cutoff current	$I_{EBO}$	$V_{EB} = -4V$			-0.5	$\mu A$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -0.5A, I_B = -50mA$			-0.5	V
DC current transfer ratio	$h_{FE}$	$V_{CE} = -3V, I_C = -100mA$	120		390	
Output Capacitance	$C_{ob}$	$V_{CB} = -10V, I_E = 0A, f = 1MHz$		12	30	pF
Transition frequency	$f_T$	$V_{CE} = -5V, I_E = 50mA, f = 100MHz$		200		MHz

### hFE Classification

Marking	AHQ	AHR
Rank	Q	R
hFE	120~270	180~390